UNR1231 (UN1231), UNR1231A (UN1231A)

Silicon NPN epitaxial planar type

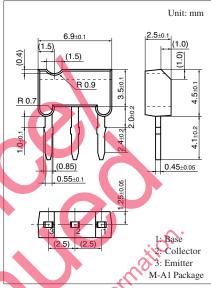
For amplification of the low frequency

Features

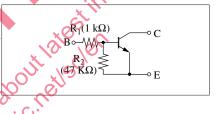
- High forward current transfer ratio h_{FE}
- M type mold package
- · Costs can be reduced through downsizing of the equipment and reduction of the number of parts.

Absolute Maximum Ratings $T_a = 25^{\circ}C$

Paramete	Symbol	Rating	Unit	
Collector-base voltage	UNR1231	V _{CBO}	20	V
(Emitter open)	UNR1231A		60	
Collector-emitter voltage	UNR1231	V _{CEO}	20	V
(Base open)	UNR1231A		50	
Collector current	I _C	0.7	Α	
Peak collector current	I _{CP}	1.5	A	
Total power dissipatio	P _T	1.0	W	
Junction temperature	Tj	150	°C	
Storage temperature	T _{stg}	-55 to +150	°C	



Internal Connection



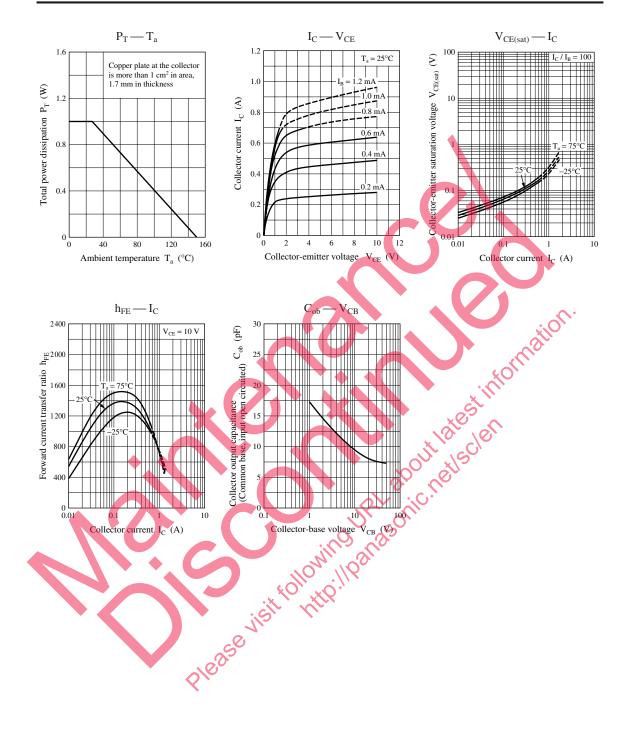
$5^{\circ}C \pm 3^{\circ}C$ Electrical Characteristics

-1		<u>∧</u> B⊶∖							
Storage temperature T_{stg} -55 to +150 °C $R_2 \ge$									
Note) *: Printed circuit board: Copper foil area of 1 cm ² or more, and the $(47 \text{ K}\Omega)$ \frown E									
board thickness of 1.7 mm for the collector portion									
Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$									
Symbol	Conditions	Min	Тур	Max	Unit				
V _{CBO}	$I_{\rm Q} = 10 \ \mu A, \ I_{\rm E} = 0$	20			V				
		60							
V _{CEO}	$I_{\rm C} = 1 \text{ mA}, I_{\rm B} = 0$	20			V				
e la		50							
I _{CBO}	$V_{CB} = 15 \text{ V}, I_E = 0$			1	μΑ				
I _{CEO}	$V_{CE} = 15 \text{ V}, I_B = 0$			10	μΑ				
I _{EBO}	$V_{EB} = 14 V, I_C = 0$			0.5	mA				
h _{FE}	$V_{CE} = 10 \text{ V}, I_C = 150 \text{ mA}$	800		2100	—				
V _{CE(sat)}	$I_{C} = 500 \text{ mA}, I_{B} = 5 \text{ mA}$			0.4	V				
f _T	$V_{CB} = 20 \text{ V}, I_E = -20 \text{ mA}, f = 200 \text{ MHz}$		55		MHz				
R ₁		0.7	1	1.3	V				
R ₁ /R ₂		0.016	0.021	0.025					
	$T_{stg} = -$ il area of 1 he collector $T_{cB0} = -$ T	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	T _{stg} -55 to +150 °C R3 it area of 1 cm ² or more, and the ne collector portion (47 KS) Symbol Conditions Min V _{CB0} I _G = 10 µA, I _E = 0 20 60 V _{CE0} I _G = 10 µA, I _E = 0 20 V _{CB0} I _G = 15 V, I _E = 0 20 I _{CE0} V _{CE} = 15 V, I _E = 0 50 I _{CE0} V _{CE} = 15 V, I _E = 0 50 I _{EB0} V _{EB} = 14 V, I _C = 0 800 V _{CE(sat)} I _C = 500 mA, I _B = 5 mA 800 V _{CE(sat)} I _C = 500 mA, I _B = 5 mA 0.7 R ₁ 0.7	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $				

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors. 2. *: Pulse measurement

Note) The part numbers in the parenthesis show conventional part number.

Panasonic



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